

# 2SK3878

## Switching Regulator Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 1.0 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 7.0 S$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 720 V$ )
- Enhancement model:  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	900	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	900	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	9	A
	Pulse (Note 1)	$I_{DP}$	27	
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	150	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	778	mJ
Avalanche current		$I_{AR}$	9	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	15	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	$-55 \sim 150$	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.833	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

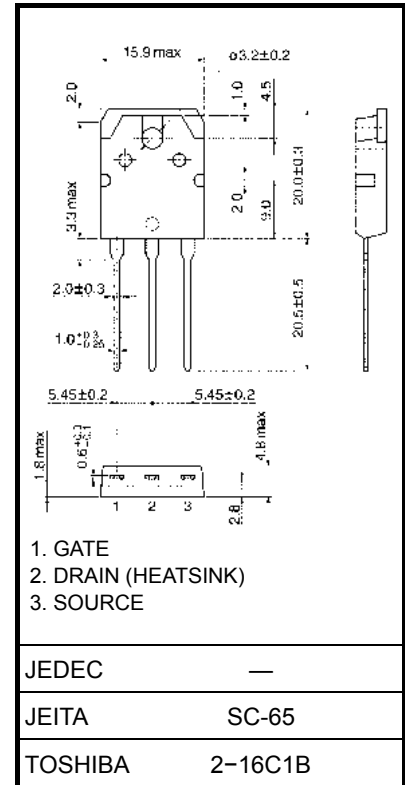
Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$  during use of the device.

Note 2:  $V_{DD} = 90 V, T_{ch} = 25^\circ C, L = 17.6 mH, R_G = 25 \Omega, I_{AR} = 9 A$

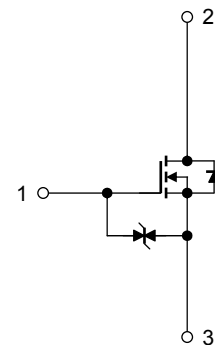
Note 3: Repetitive rating: pulse width limited by max junction temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 4.6 g (typ.)



## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	$\pm 30$	—	—	V
Drain cutoff current		$I_{DSS}$	$V_{DS} = 720 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	900	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$	—	1.0	1.3	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 15 \text{ V}, I_D = 4 \text{ A}$	3.5	7.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	2200	—	pF
Reverse transfer capacitance		$C_{rss}$		—	45	—	
Output capacitance		$C_{oss}$		—	190	—	
Switching time	Rise time	$t_r$		—	25	—	ns
	Turn-on time	$t_{on}$		—	65	—	
	Fall time	$t_f$		—	20	—	
	Turn-off time	$t_{off}$		—	120	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$	—	60	—	nC
Gate-source charge		$Q_{gs}$		—	34	—	
Gate-drain ("Miller") charge		$Q_{gd}$		—	26	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	9	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	27	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 9 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 9 \text{ A}, V_{GS} = 0 \text{ V}$ ,	—	1.4	—	$\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	16	—	$\mu\text{C}$

## Marking

